

General Description

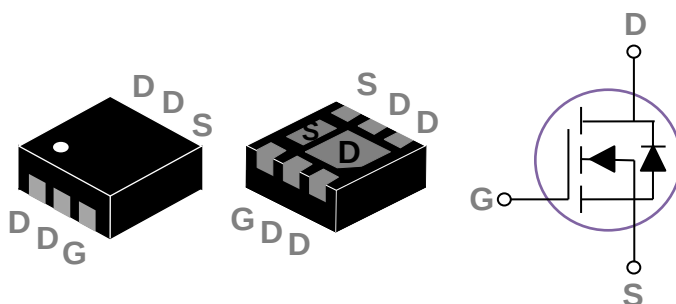
These N-Channel enhancement mode power field effect transistors are using trench DMOS technology. This advanced technology has been especially tailored to minimize on-state resistance, provide superior switching performance, and withstand high energy pulse in the avalanche and commutation mode. These devices are well suited for high efficiency fast switching applications.

BVDSS	RDS(on)	ID
30V	19mΩ	8A

Features

- 30V, 8A, $R_{DS(ON)} = 19m\Omega$ @ $V_{GS} = 10V$
- Improved dv/dt capability
- Fast switching
- Green Device Available

DFN2x2-6L 2EP Pin Configuration



Applications

- MB / VGA / Vcore
- POL Applications
- SMPS 2nd SR

Absolute Maximum Ratings $T_c=25^\circ\text{C}$ unless otherwise noted

Symbol	Parameter	Rating	Units
V_{DS}	Drain-Source Voltage	30	V
V_{GS}	Gate-Source Voltage	± 20	V
I_D	Drain Current – Continuous ($T_A=25^\circ\text{C}$)	8	A
	Drain Current – Continuous ($T_A=70^\circ\text{C}$)	6.4	A
I_{DM}	Drain Current – Pulsed ¹	32	A
P_D	Power Dissipation ($T_A=25^\circ\text{C}$)	2	W
	Power Dissipation – Derate above 25°C	16.1	mW/ $^\circ\text{C}$
T_{STG}	Storage Temperature Range	-55 to 150	$^\circ\text{C}$
T_J	Operating Junction Temperature Range	-55 to 150	$^\circ\text{C}$

Thermal Characteristics

Symbol	Parameter	Typ.	Max.	Unit
$R_{\theta JA}$	Thermal Resistance Junction to ambient	---	62	$^\circ\text{C/W}$

Electrical Characteristics ($T_J=25^\circ\text{C}$, unless otherwise noted)
Off Characteristics

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
BV_{DSS}	Drain-Source Breakdown Voltage	$V_{GS}=0V$, $I_D=250\mu A$	30	---	---	V
$\Delta BV_{DSS}/\Delta T_J$	BV_{DSS} Temperature Coefficient	Reference to 25°C , $I_D=1mA$	---	0.04	---	$V/^\circ\text{C}$
I_{DSS}	Drain-Source Leakage Current	$V_{DS}=30V$, $V_{GS}=0V$, $T_J=25^\circ\text{C}$	---	---	1	μA
		$V_{DS}=24V$, $V_{GS}=0V$, $T_J=125^\circ\text{C}$	---	---	10	μA
I_{GSS}	Gate-Source Leakage Current	$V_{GS}=\pm 20V$, $V_{DS}=0V$	---	---	± 100	nA

On Characteristics

$R_{DS(ON)}$	Static Drain-Source On-Resistance ³	$V_{GS}=10V$, $I_D=4A$	---	15.5	19	$m\Omega$
		$V_{GS}=4.5V$, $I_D=3A$	---	20.5	27	$m\Omega$
$V_{GS(th)}$	Gate Threshold Voltage	$V_{GS}=V_{DS}$, $I_D=250\mu A$	1.2	1.6	2.5	V
$\Delta V_{GS(th)}$	$V_{GS(th)}$ Temperature Coefficient		---	-4	---	$mV/^\circ\text{C}$
g_{fs}	Forward Transconductance	$V_{DS}=10V$, $I_D=2A$	---	4	---	S

Dynamic and switching Characteristics

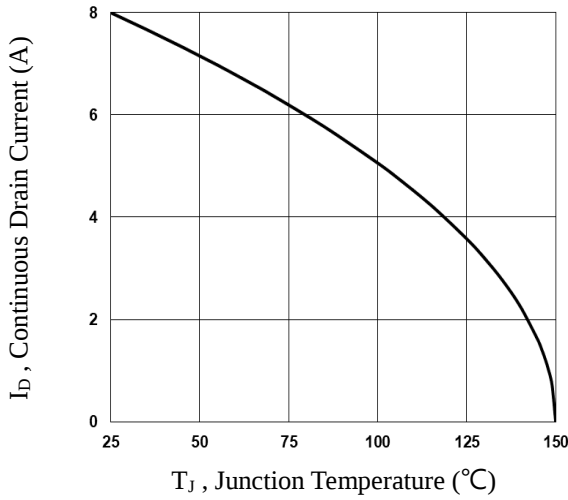
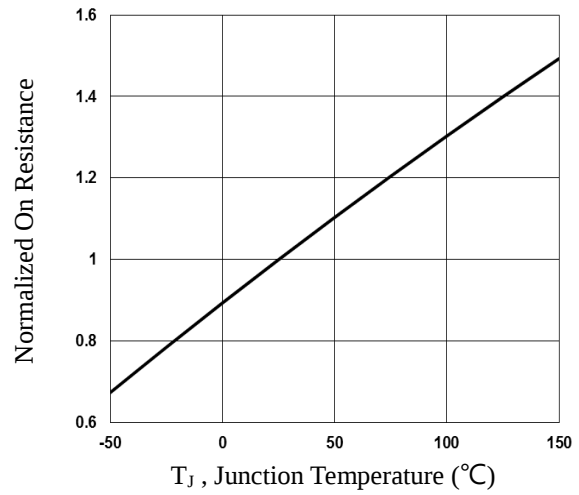
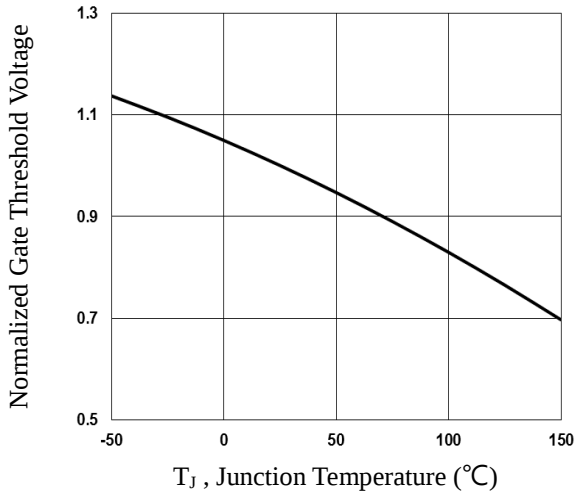
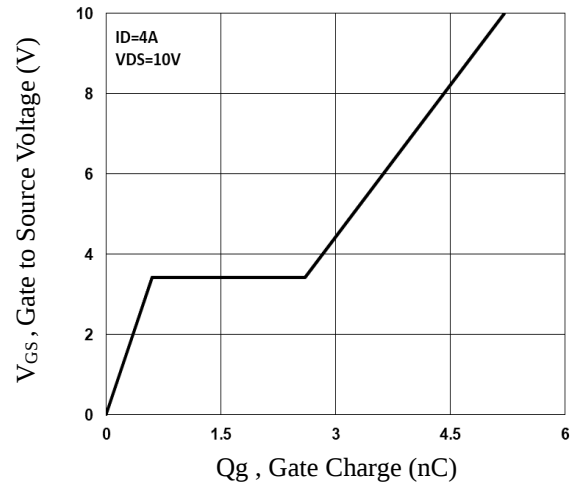
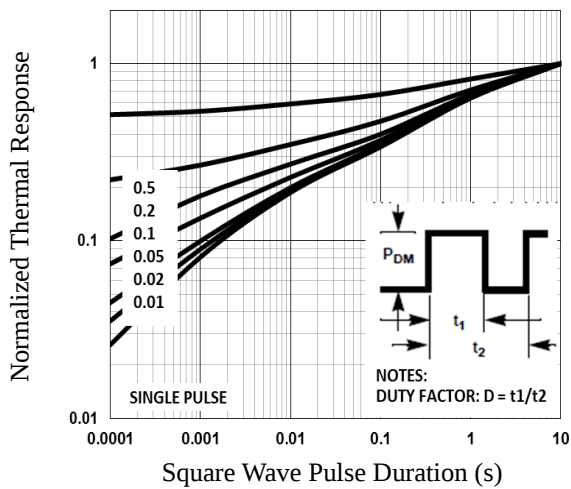
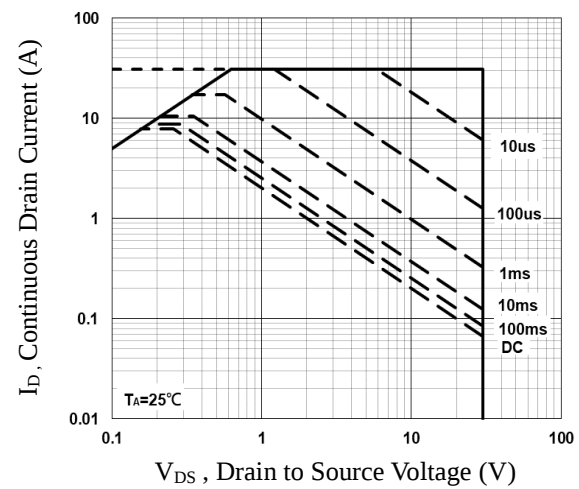
Q_g	Total Gate Charge ^{2, 3}	$V_{DS}=15V$, $V_{GS}=10V$, $I_D=4A$	---	5.2	7.8	nC
Q_{gs}	Gate-Source Charge ^{2, 3}		---	0.6	0.9	
Q_{gd}	Gate-Drain Charge ^{2, 3}		---	2	3	
$T_{d(on)}$	Turn-On Delay Time ^{2, 3}	$V_{DD}=15V$, $V_{GS}=10V$, $R_G=6\Omega$ $I_D=4A$	---	2.8	4.2	ns
T_r	Rise Time ^{2, 3}		---	7.2	11	
$T_{d(off)}$	Turn-Off Delay Time ^{2, 3}		---	15.8	24	
T_f	Fall Time ^{2, 3}		---	4.6	7	
C_{iss}	Input Capacitance	$V_{DS}=15V$, $V_{GS}=0V$, $F=1MHz$	---	490	750	pF
C_{oss}	Output Capacitance		---	80	120	
C_{rss}	Reverse Transfer Capacitance		---	55	90	
R_g	Gate resistance	$V_{GS}=0V$, $V_{DS}=0V$, $f=1MHz$	---	2.2	---	Ω

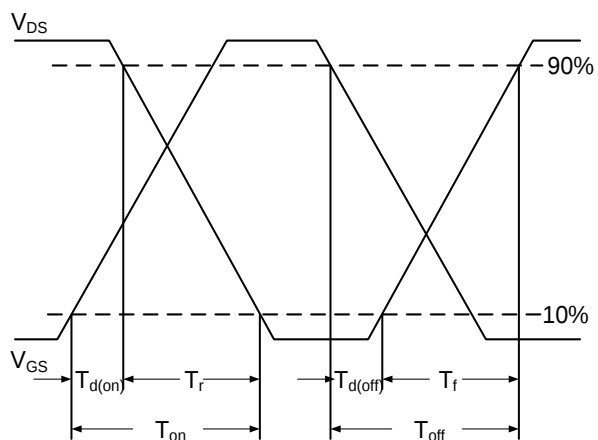
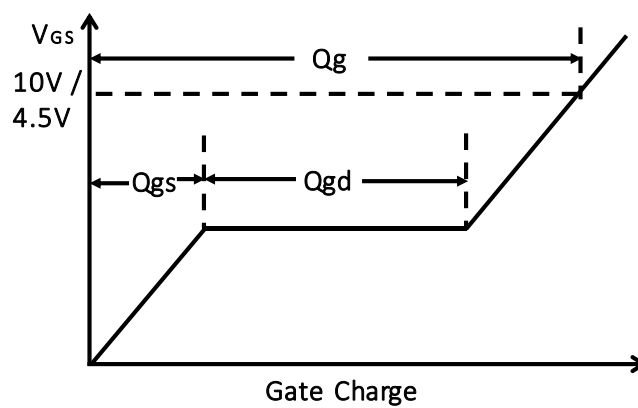
Drain-Source Diode Characteristics and Maximum Ratings

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
I_S	Continuous Source Current	$V_G=V_D=0V$, Force Current	---	---	8	A
I_{SM}	Pulsed Source Current ³		---	---	16	A
V_{SD}	Diode Forward Voltage ³	$V_{GS}=0V$, $I_S=1A$, $T_J=25^\circ\text{C}$	---	---	1	V
t_{rr}	Reverse Recovery Time	$V_R=30V$, $I_S=8A$	---	130	---	ns
Q_{rr}	Reverse Recovery Charge	$di/dt=100A/\mu s$, $T_J=25^\circ\text{C}$	---	200	---	nC

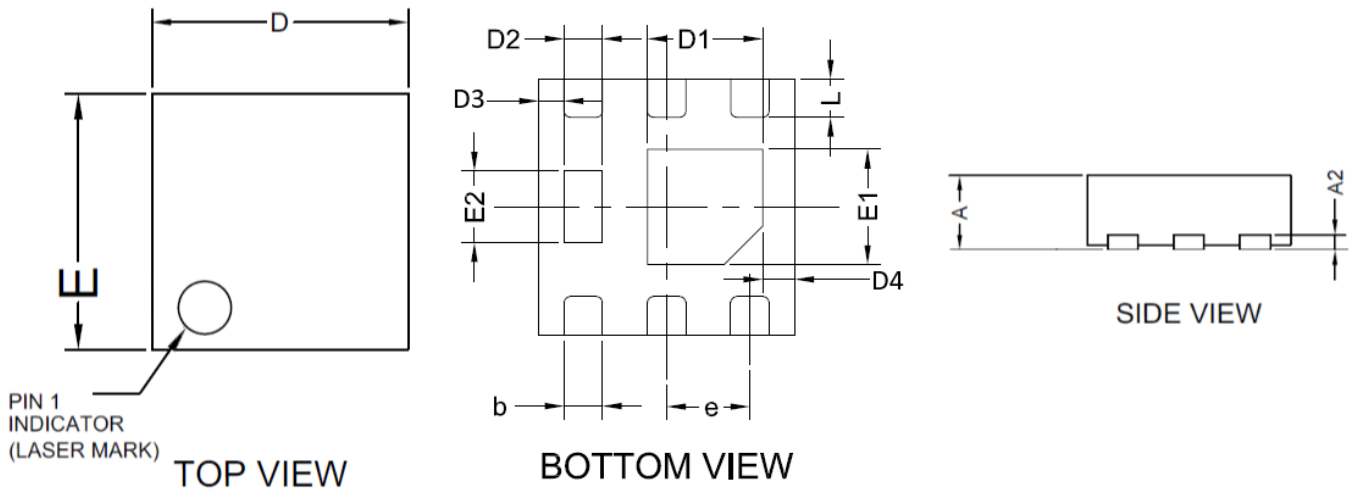
Note :

1. Repetitive Rating : Pulsed width limited by maximum junction temperature.
2. The data tested by pulsed , pulse width $\leq 300\mu s$, duty cycle $\leq 2\%$.
3. Essentially independent of operating temperature.


Fig.1 Continuous Drain Current vs. T_J

Fig.2 Normalized $R_{DS(on)}$ vs. T_J

Fig.3 Normalized V_{th} vs. T_J

Fig.4 Gate Charge Waveform

Fig.5 Normalized Transient Response

Fig.6 Maximum Safe Operation Area


Fig.7 Switching Time Waveform

Fig.8 Gate Charge Waveform

DFN2x2-6L 2EP PACKAGE INFORMATION



Symbol	Dimensions In Millimeters		Dimensions In Inches	
	MAX	MIN	MAX	MIN
A	0.800	0.500	0.031	0.019
A2	0.250	0.145	0.010	0.006
b	0.350	0.250	0.014	0.010
D	2.100	1.900	0.083	0.075
D1	1.050	0.800	0.041	0.031
D2	0.430	0.250	0.017	0.010
D3	0.200BSC		0.008BSC	
D4	0.200BSC		0.008BSC	
E	2.100	1.900	0.083	0.075
E1	1.250	0.800	0.049	0.031
E2	0.750	0.460	0.029	0.018
e	0.650BSC		0.026BSC	
L	0.350	0.225	0.014	0.009

RECOMMENDED LAND PATTERN

DFN2X2-6L 2EP

